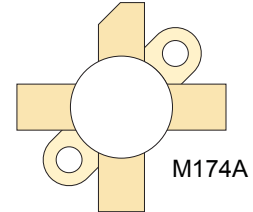



RF POWER VERTICAL MOSFET

The VRF151E is a thermally-enhanced version of the VRF151. It is a gold-metallized silicon n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, or inter-modulation distortion.



FEATURES

- Enhanced Package for 30% higher P_D
- Improved Ruggedness $V_{(BR)DSS} = 170V$
- 150W with 22dB Typical Gain @ 30MHz, 50V
- 150W with 14dB Typical Gain @ 175MHz, 50V
- Excellent Stability & Low IMD
- Available in Matched Pairs
- 30:1 Load VSWR Capability at Specified Operating Conditions
- Nitride Passivated
- Refractory Gold Metallization
- Replacement for SD2931-10 w/higher BV
- RoHS Compliant 

Maximum Ratings

All Ratings: $T_c = 25^\circ C$ unless otherwise specified


Symbol	Parameter	VRF151E(MP)	Unit
V_{DSS}	Drain-Source Voltage	170	V
I_D	Continuous Drain Current @ $T_c = 25^\circ C$	16	A
V_{GS}	Gate-Source Voltage	± 40	V
P_D	Total Device dissipation @ $T_c = 25^\circ C$	390	W
T_{STG}	Storage Temperature Range	-65 to 150	°C
T_J	Operating Junction Temperature	200	

Static Electrical Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 100mA$)	170	180		V
$V_{DS(ON)}$	On State Drain Voltage ($I_{D(ON)} = 10A, V_{GS} = 10V$)		2.0	3.0	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 100V, V_{GS} = 0V$)			1	mA
I_{GSS}	Gate-Source Leakage Current ($V_{DS} = \pm 20V, V_{GS} = 0V$)			1.0	μA
g_{fs}	Forward Transconductance ($V_{DS} = 10V, I_D = 5A$)	5.0			mhos
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = 10V, I_D = 100mA$)	2.9	3.6	4.4	V

Thermal Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.45	°C/W

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Dynamic Characteristics

VRF151E(MP)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 150V$ $f = 1MHz$		375		pF
C_{oss}	Output Capacitance			200		
C_{rss}	Reverse Transfer Capacitance			12		

Functional Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
G_{PS}	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$	18	22		dB
G_{PS}	$f = 175MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W$		14		
η_D	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		50		%
IMD _(d3)	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}^1$		-30		dBc
IMD _(d11)	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		-60		
Ψ	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$ 30:1 VSWR - All Phase Angles	No Degradation in Output Power			

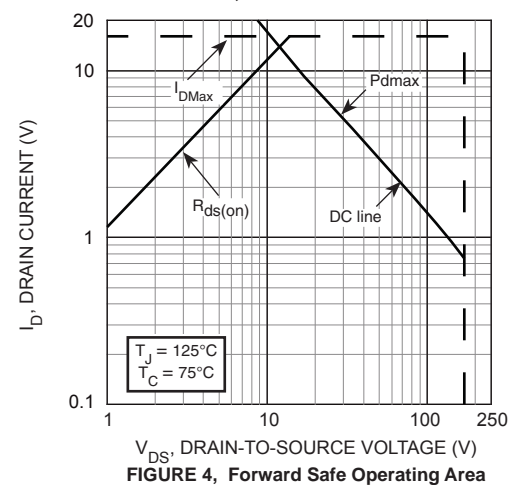
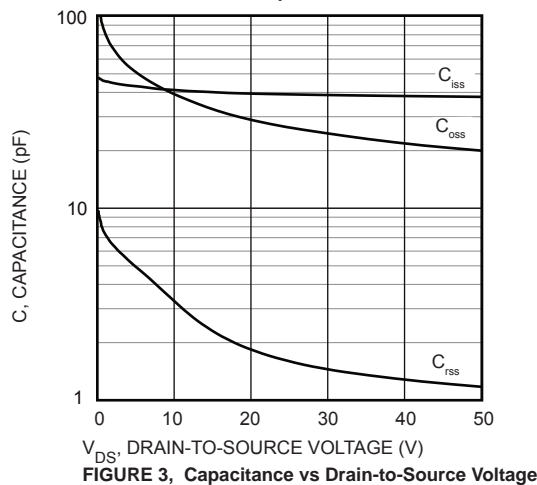
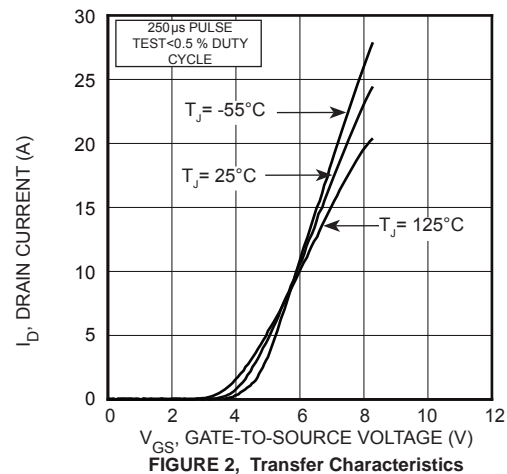
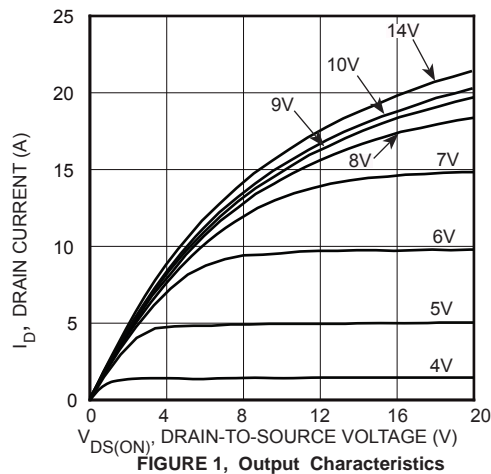
Class A Characteristics

Symbol	Test Conditions	Min	Typ	Max	Unit
G_{PS}	$f = 30MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		20		dB
IMD _(d3)	$f = 30MHz, V_{DD} = 50V, I_{DQ}(\text{Max}) = 3.75A, P_{out} = 150W_{PEP}$		-50		
IMD _(d9-d13)	$f = 30MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		-75		

1. To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves



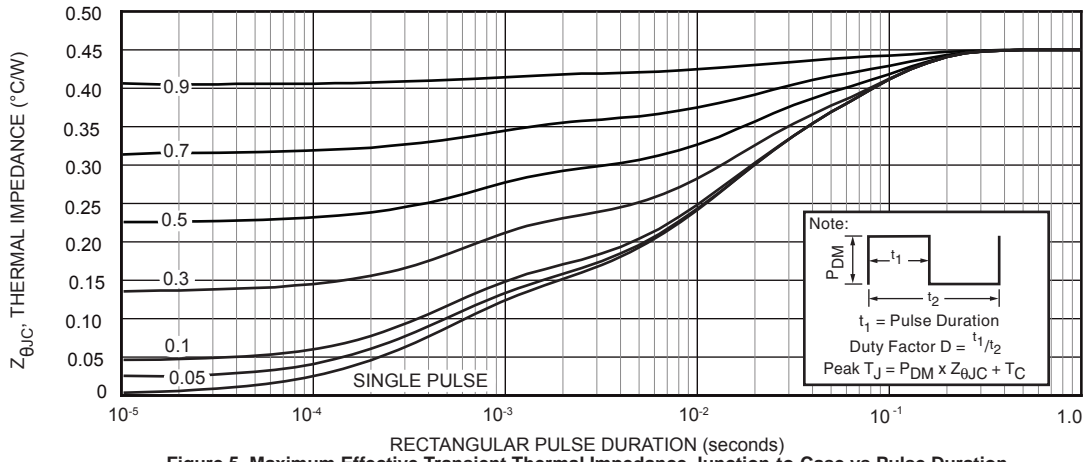


Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

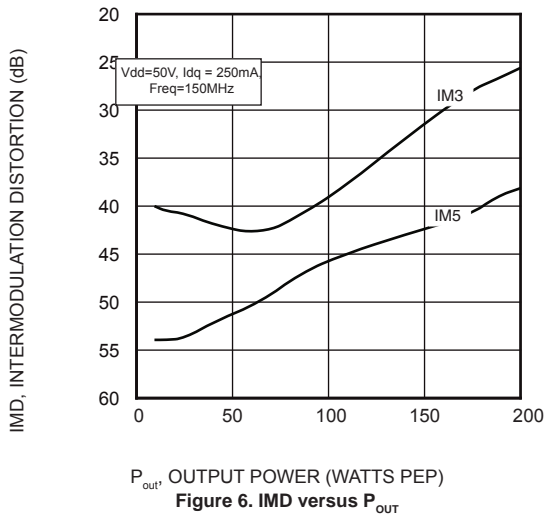


Figure 6. IMD versus P_{OUT}

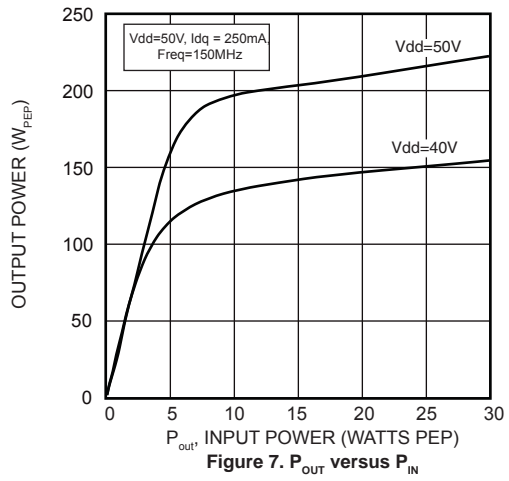
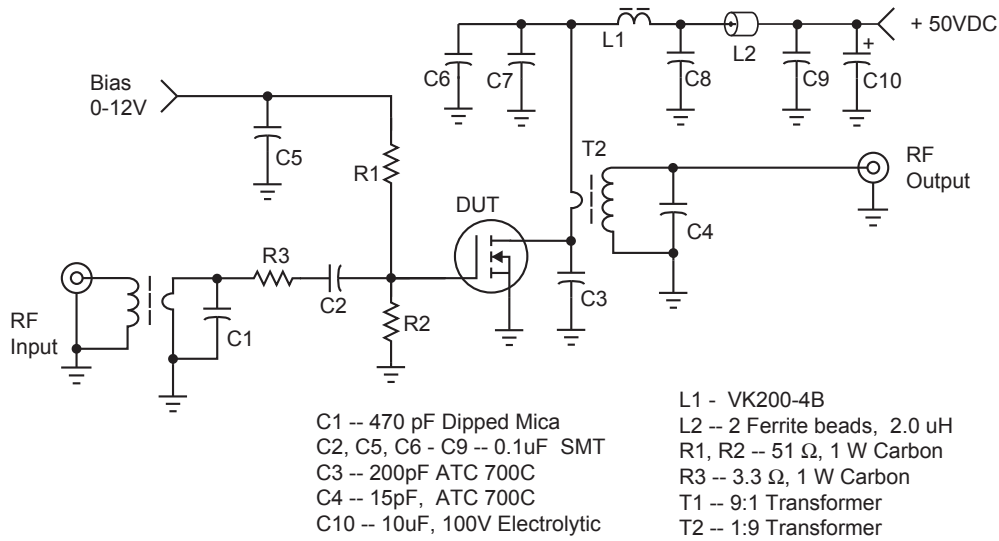
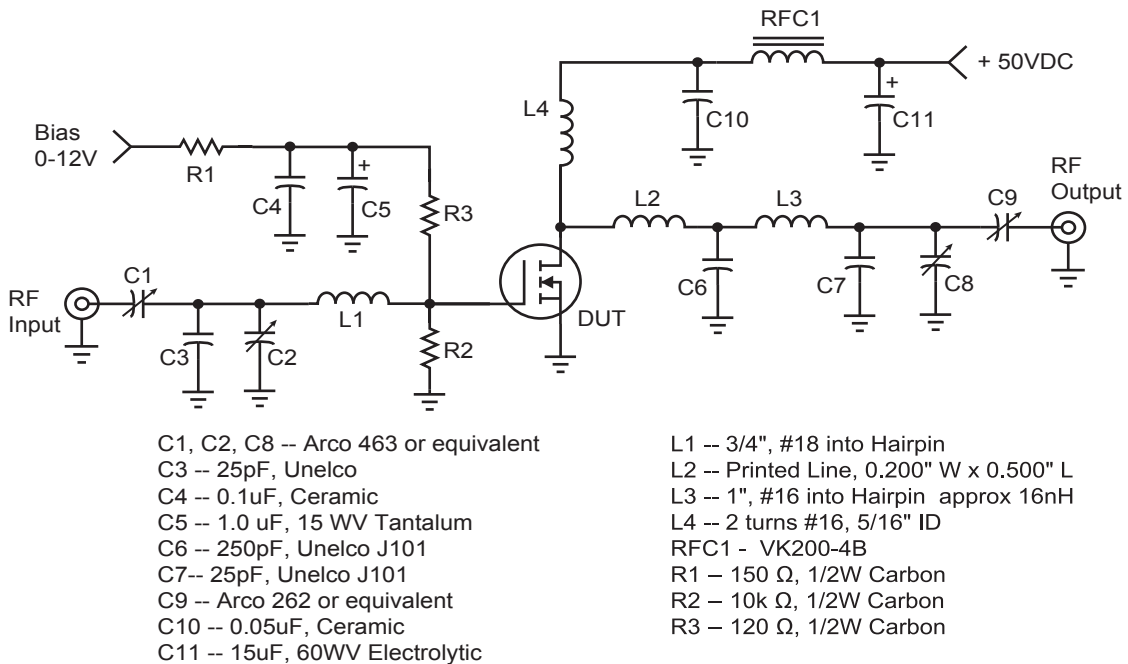


Figure 7. P_{OUT} versus P_{IN}

30 MHz test Circuit



175 MHz test Circuit

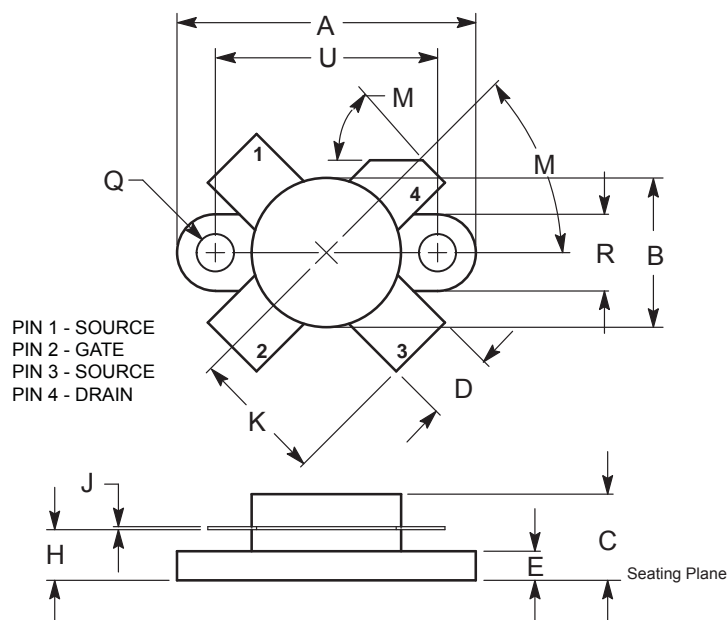


Adding MP at the end of P/N specifies a matched pair where $V_{GS(TH)}$ is matched between the two parts. V_{TH} values are marked on the devices per the following table.

Code	Vth Range	Code 2	Vth Range
A	2.900 - 2.975	M	3.650 - 3.725
B	2.975 - 3.050	N	3.725 - 3.800
C	3.050 - 3.125	P	3.800 - 3.875
D	3.125 - 3.200	R	3.875 - 3.950
E	3.200 - 3.275	S	3.950 - 4.025
F	3.275 - 3.350	T	4.025 - 4.100
G	3.350 - 3.425	W	4.100 - 4.175
H	3.425 - 3.500	X	4.175 - 4.250
J	3.500 - 3.575	Y	4.250 - 4.325
K	3.575 - 3.650	Z	4.325 - 4.400

V_{TH} values are based on Microsemi measurements at datasheet conditions with an accuracy of 1.0%.

.5" SOE Package Outline
All Dimensions are ± .005



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.096	0.990	24.39	25.14
B	0.465	0.510	11.82	12.95
C	0.229	0.275	5.82	6.98
D	0.216	0.235	5.49	5.96
E	0.084	0.110	2.14	2.79
H	0.144	0.178	3.66	4.52
J	0.003	0.007	0.08	0.17
K	0.435		11.0	
M	45° NOM		45° NOM	
Q	0.115	0.130	2.93	3.30
R	0.246	0.255	6.25	6.47
U	0.720	0.730	18.29	18.54

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743, 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. US and Foreign patents pending. All Rights Reserved.